2SC2733

Silicon NPN Epitaxial

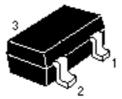
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Application

VHF frequency converter

Outline

MPAK



- 1. Emitter
- 2.Base
- 3. Collector



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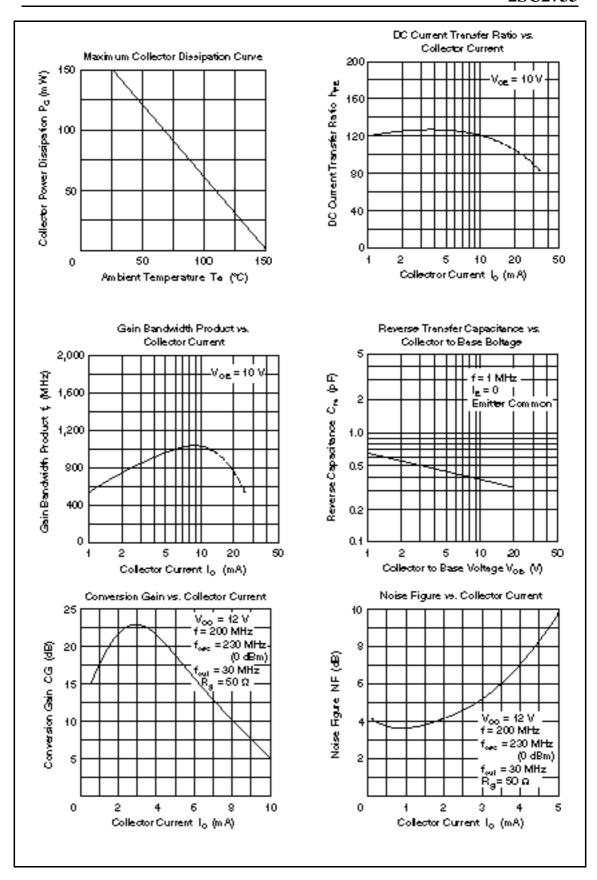
Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

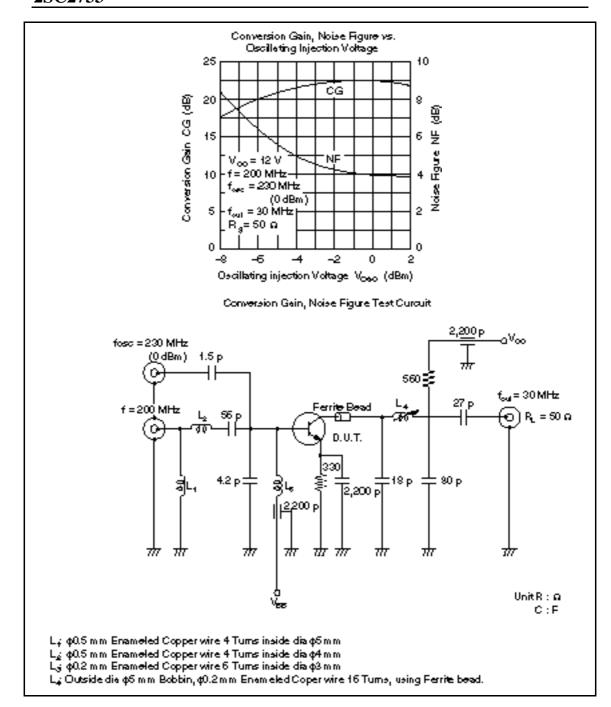
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	30	V
Collector to emitter voltage	V_{CEO}	20	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I _c	50	mA
Collector power dissipation	P _c	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	_	_	V	$I_{\rm C} = 10 \ \mu {\rm A}, \ I_{\rm E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	20	_	_	V	$I_c = 1 \text{ mA}, R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	3	_	_	V	$I_{E} = 10 \ \mu A, \ I_{E} = 0$
Collector cutoff current	I _{CBO}	_	_	0.5	μΑ	$V_{CB} = 10 \text{ V}, I_{C} = 0$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	1.0	V	$I_{\rm C}$ = 20 mA, $I_{\rm B}$ = 4 mA
DC current transfer ratio	h_{FE}	60	120	_		V_{CE} = 10 V, I_{C} = 10 mA
Gain bandwidth product	f _T	600	1000	_	MHz	$V_{CE} = 10 \text{ V}, I_{C} = 10 \text{ mA}$
Collector output capacitance	Cob	_	0.35	0.65	pF	$V_{CB} = 10 \text{ V}$, Emitter ground, $f = 1 \text{ MHz}$
Conversion gain	CG	_	21	_	dB	V_{CC} = 12 V, I_{C} = 2 mA, f = 200 MHz, f_{OSC} = 230 MHz (0dBm), f_{out} = 30 MHz
Noise figure	NF	_	4.0	_	dB	V_{CC} = 12 V, I_{C} = 2 mA, f = 200 MHz, f_{OSC} = 230 MHz (0dBm), f_{out} = 30 MHz

Note: Marking is "HC".





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